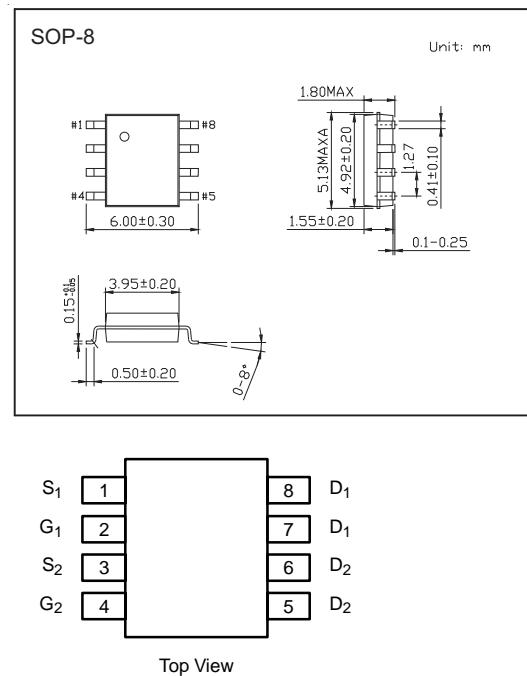
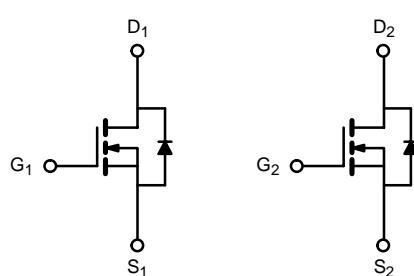


Dual N-Channel MOSFET

KI9926A

■ Features

- $R_{DS(on)} = 0.030 \Omega$ @ $V_{GS} = 4.5 V$
- $R_{DS(on)} = 0.040 \Omega$ @ $V_{GS} = 2.5 V$.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current *1 $T_A=25^\circ C$	I_D	4.8	A
		3.8	A
Pulsed Drain Current	I_{DM}	30	A
Maximum Power Dissipation *1 $T_A = 25^\circ C$	P_D	1.25	W
		0.8	W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	100	$^\circ C/W$
Maximum Junction-to-Foot (Drain)	$R_{\theta JF}$	40	$^\circ C/W$
Junction temperature and Storage temperature	T_j, T_{stg}	-55 to +150	$^\circ C$

*1 Surface Mounted on 1" x 1" FR4 Board.

KI9926A■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu \text{ A}$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$		1		uA
		$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, T_J = 55^\circ\text{C}$			25	
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 12\text{V}$			± 100	nA
Drain-Source On-State Resistance *2	$r_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 6.5\text{A}$		0.023	0.030	Ω
		$V_{GS} = 2.5\text{V}, I_D = 5.4\text{A}$		0.030	0.040	
On-State Drain Current *2	$I_{D(on)}$	$V_{DS} = 5\text{V}, V_{GS} = 4.5\text{V}$	20			A
Forward Transconductance *2	g_{fs}	$V_{DS} = 15\text{V}, I_D = 6\text{A}$		22		S
Total Gate Charge	Q_g	$V_{DS} = 15\text{V}, V_{GS} = 4.5\text{V}, I_D = 6\text{A}$		13	20	nC
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			3.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$ $I_D \geq 1 \text{ A}, V_{GEN} = 4.5\text{V}, R_G = 6 \Omega$		22	35	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			50	75	
Fall Time	t_f			20	30	
Continuous Source Current (Diode Conduction)	I_s				1	A
Diode Forward Voltage *2	V_{SD}	$I_s = 1.7\text{A}, V_{GS} = 0 \text{ V}$		0.7	1.2	V

*2 Pulse test; pulse width $\leq 300 \mu \text{ s}$, duty cycle $\leq 2 \%$.